

Description

The HXY5N10MI uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 100V I_{D} = 5A$

 $R_{DS(ON)} < 98 \text{ m}\Omega @ V_{GS}=10V$

 $R_{DS(ON)} < 120m\Omega @ V_{GS}=4.5V$

Application

Battery protection

Load switch

Uninterruptible power supply

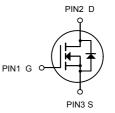
Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY5N10MI	SOT23-3L	1005	3000

Absolute Maximum Ratings (T_A=25[°]C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	100	V
VGS	Gate-Source Voltage	±20	V
lD	Drain Current-Continuous	5	A
IDM	Drain Current-Pulsed (Note 1)	20	A
PD	Maximum Power Dissipation	1.5	W
TJ,TSTG	G Operating Junction and Storage Temperature Range -55 To 175		°C
RθJA	Thermal Resistance, Junction-to-Ambient (Note 2)	100	°C /W
		1	1





N-Channel MOSFET



N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100	-	-	V
Zero Gate Voltage Drain Current	ldss	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	lgss	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)				I		
Gate Threshold Voltage	VGS(th)	Vos=Vgs,Io=250µA	1.0	1.5	2.0	V
		V_{GS} =10V, I _D =3A	-	89	98	mΩ
Drain-Source On-State Resistance	Rds(on)	V_{GS} =4.5V, I _D =3A	-	102	110	
Forward Transconductance	gfs	V _{DS} =5V,I _D =3A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	650	-	PF
Output Capacitance	Coss	V _{DS} =50V,V _{GS} =0V,	-	24	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	20	-	PF
Switching Characteristics (Note 4)				I		
Turn-on Delay Time	td(on)		-	6	-	nS
Turn-on Rise Time	tr	V _{DD} =50V, R _L =19Ω	-	4	-	nS
Turn-Off Delay Time	td(off)	V _{GS} =10V,R _G =3Ω	-	20	-	nS
Turn-Off Fall Time	tf		-	4	-	nS
Total Gate Charge	Qg		-	20		nC
Gate-Source Charge	Qgs	V _{DS} =50V,I _D =3A,	-	2.1	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.3	-	nC
Drain-Source Diode Characteristics	I					
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	ls		-	-	3	А

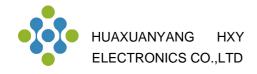
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t \leq 10 sec.

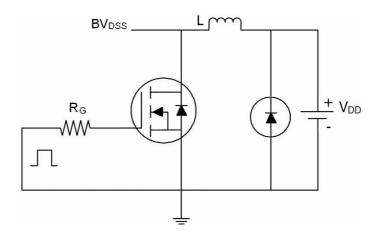
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

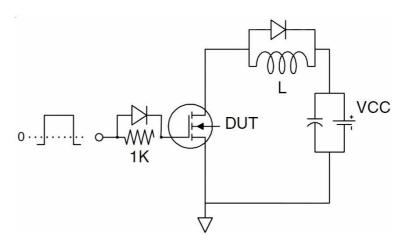


Test Circuit

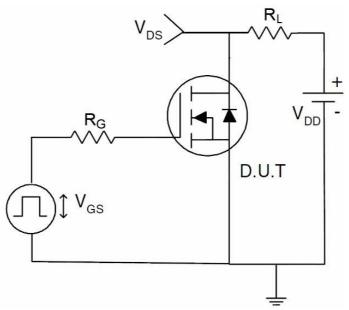
1) E_{AS} test circuit

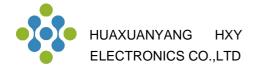


2) Gate charge test circuit

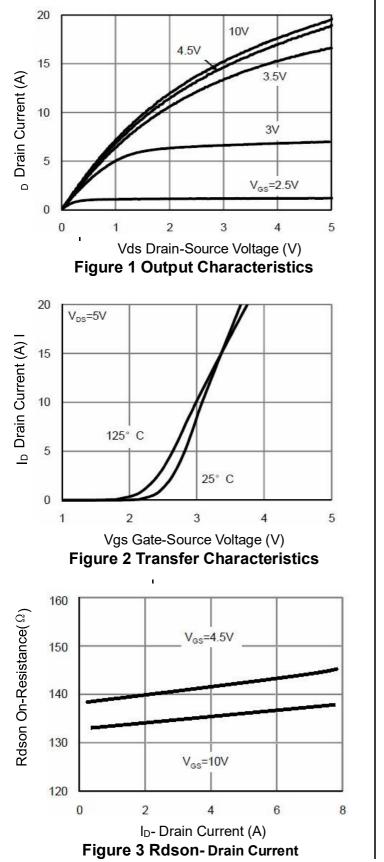


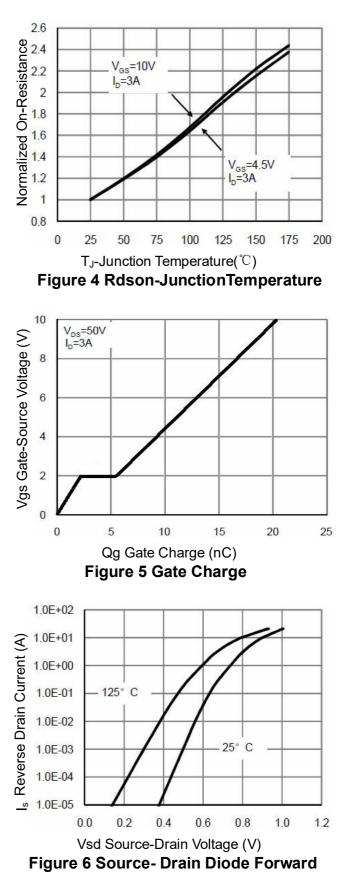
3) Switch Time Test Circuit

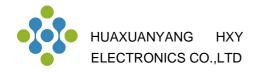




Typical Electrical and Thermal Characteristics (Curves)







HXY5N10MI N-Channel Enhancement Mode MOSFET

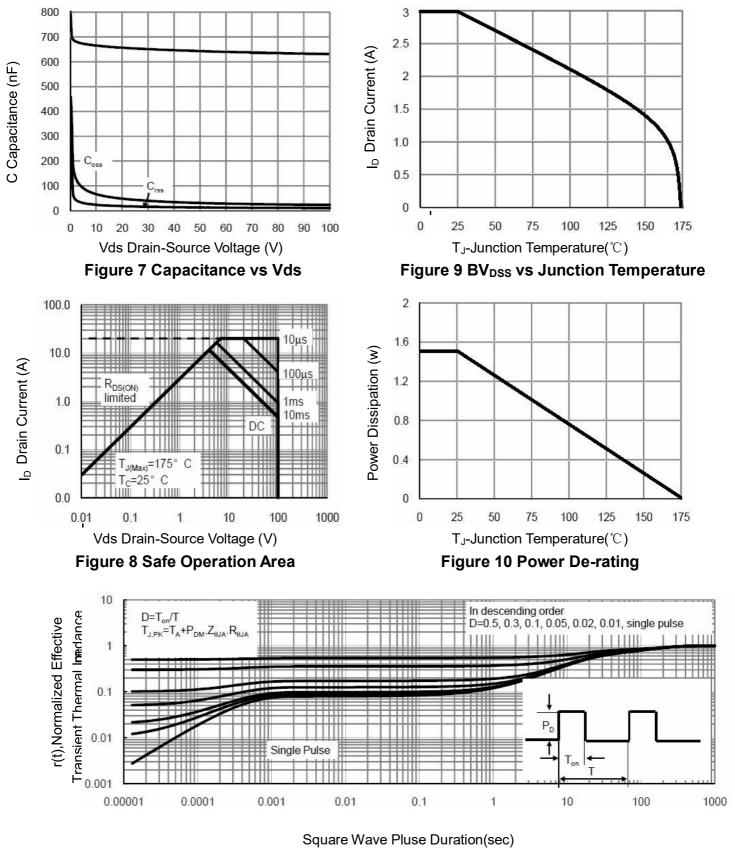
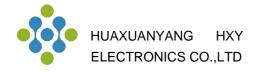
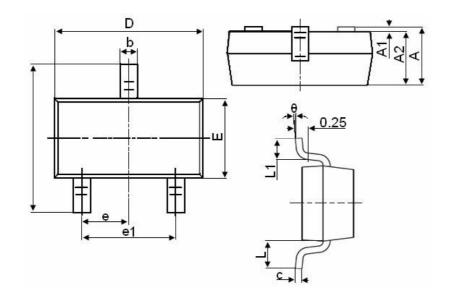


Figure 11 Normalized Maximum Transient Thermal Impedance



SOT23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
A	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
с	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



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